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(72) Inventors; and

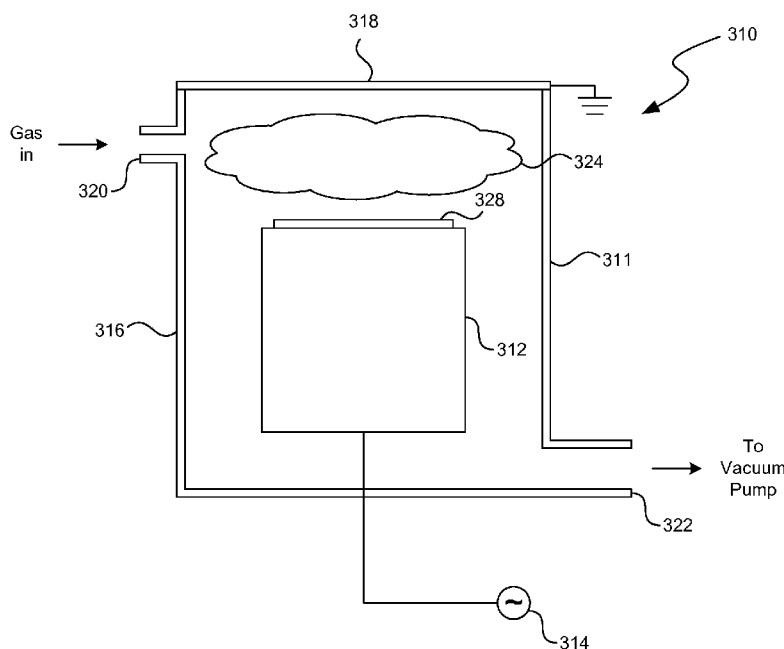
(75) Inventors/Applicants (for US only): **REN, Zaiyuan** [CN/US]; 3308 S. Gekeler Lane, Apt. E101, Boise, ID 83706 (US). **GEHRKE, Thomas** [DE/US]; 5823 E. Gateway Drive, Boise, ID 83716 (US).(74) Agents: **LIANG, Chen** et al.; Perkins Coie LLP, P.O. Box 1247, Seattle, WA 98111-1247 (US).

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(54) Title: LIGHT EMITTING DIODES WITH N-POLARITY AND ASSOCIATED METHODS OF MANUFACTURING

**FIG. 3B**

(57) Abstract: Light emitting diodes ("LEDs") with N-polarity and associated methods of manufacturing are disclosed herein. In one embodiment, a method for forming a light emitting diode on a substrate having a substrate material includes forming a nitrogen-rich environment at least proximate a surface of the substrate without forming a nitriding product of the substrate material on the surface of the substrate. The method also includes forming an LED structure with a nitrogen polarity on the surface of the substrate with a nitrogen-rich environment.



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